

Table of Contents

	Page
Acknowledgment	i
Abstract of the Thesis	
English Version	ii - iii
Malay Version	iv - v
Chapter 1 Introduction	1
1.1 Introduction	1
Chapter 2 Background Theory and Literature Review	5
2.1 Introduction	5
2.2 Metal-Oxide-Semiconductor (MOS) Device	5
2.2.1 MOS Structure	5
2.2.2 Energy Band Profile of MOS Junction	6
2.2.3 MOS Characteristics	12
2.2.3-1 Threshold Voltage	12
2.2.3-2 Capacitance-Voltage (C-V)	14
2.2.3-3 Non-Ideal MOS Structure	17
2.3 Field-Effect Transistor (FET)	24 -
2.3.1 Metal-Oxide-Semiconductor Field-Effect Transistor (MOSFET)	26
2.3.1-1 MOSFET Structure	26
2.3.1-2 Energy Band Profile and Principle of Operation	27
2.3.1-3 Current-Voltage Characteristic	29

	2.3.1-4	Types of MOSFET	32
	2.3.2	Junction Field-Effect Transistor (JFET)	34
	2.3.2-1	JFET Structure	34
	2.3.2-2	Band Energy Profile and Principle of Operation	37
	2.3.2-3	Current-Voltage Characteristics	40
2.4		Power Semiconductor Devices	43
	2.4.1	Thyristor	44
	2.4.2	Power Bipolar Junction Transistor (BJT)	46
	2.4.3	Power MOSFET	48
	2.4.3-1	Structure	48
	2.4.3-2	Principle of Operation	52
	2.4.3-3	Current-Voltage Characteristics	55
	2.4.4	Importance and Applications of Power Semiconductor Devices	56
	2.4.4-1	Comparison of “Controllable Switches Group”	56
	2.4.4-2	Power Semiconductor Device Capability	57
	2.4.4-3	Applications of Device	58
Chapter 3		High Frequency Characterization of the n-Channel Enhancement Mode Power MOSFET Device	61
	3.1	Introduction	61
	3.2	Power MOSFET Device Structure	62
	3.3	Experimental Set-up for Device Characterization	65
	3.4	Test Fixture Design	67

3.5	Capacitance-Voltage and Conductance-Voltage Measurement Techniques	70
3.6	Capacitance-Voltage and Conductance-Voltage Measurement at Elevated Temperatures	72
3.7	Annealing Process	73
3.7.1	Calibration of Furnace	73
3.7.2	Annealing Process	78

Chapter 4 High Frequency Capacitance-Voltage Measurements On The n-Channel Enhancement Mode Power Device: Results and Analysis **79**

4.1	Introduction	79
4.2	High Frequency Capacitance-Voltage Characteristics of Device	80
4.2.1	Measurements across Gate-Source Structure	80
4.2.2	Measurements across Gate-Drain Structure	87
4.2.3	Measurement across Source-Drain Structure	91
4.3	High Frequency Capacitance-Voltage Measurement Results at Different Measurement Temperatures across Gate-Source Structure	93
4.4	High Frequency Capacitance-Voltage Characteristics of Device: Effects of Annealing on Device	96
4.5	High Frequency Capacitance-Voltage Measurement Results of Device Annealed at 400°C at Different Measurement Temperatures	98

Chapter 5 High Frequency Conductance-Voltage Measurements On The n-Channel Enhancement Mode Power Device: Results and Analysis **104**

5.1	Introduction	104
5.2	High Frequency Conductance-Voltage Characteristics of Device	105
5.2.1	Measurement across Gate-Source Structure	105

5.2.2	Measurement across Gate-Drain Structure	110
5.2.3	Measurement across Source-Drain Structure	112
5.3	High Frequency Conductance-Voltage Measurement Results at Different Measurement Temperatures across Gate-Source Structure	115
5.4	High Frequency Conductance-Voltage Characteristics of Device: Effects of Annealing on Device	121
5.5	High Frequency Conductance-Voltage Measurement Results of Device Annealed at 400°C at Different Measurement Temperatures	123
Chapter 6	Conclusion and Suggestion for Further Works	129
6.1	Conclusion	129
6.2	Suggestion for Further Works	132
Appendix A	References	134
Appendix B	Error Analysis	138